

Elektrische Eigenschaften	Electrical properties			
Höchstzulässige Werte	Maximum rated values			
Periodische Vorwärts- und Rückwärts-Sperrspannung	repetitive peak forward off-state and reverse voltages	$t_{vj} = -40^{\circ}\text{C} \dots t_{vj\text{ max}}$	$V_{\text{DRM}}, V_{\text{RRM}}$	800, 1000 V 1100, 1200 v 1300, 1400* v
Vorwärts-Stoßspitzen-sperrspannung	non repetitive peak forward off-state voltage	$t_{vj} = -40^{\circ}\text{C} \dots t_{vj\text{ max}}$	$V_{\text{DSM}} = V_{\text{DRM}}$	
Rückwärts-Stoßspitzen-sperrspannung	non repetitive peak reverse voltage	$t_{vj} = +25^{\circ}\text{C} \dots t_{vj\text{ max}}$	$V_{\text{RSM}} = V_{\text{RRM}}$	+ 100 v
Durchlaßstrom-Grenzeffektivwert	RMS on-state current		I_{TRMSM}	240 A
Dauerrenzstrom	average on-state current	$t_{\text{C}} = 85^{\circ}\text{C}$ $t_{\text{C}} = 70^{\circ}\text{C}$	I_{TAVM}	120 A 152 A
Stoßstrom-Grenzwert	surge current	$t_{vj} = 25^{\circ}\text{C}, t_p = 10\text{ ms}$ $t_{vj} = t_{vj\text{ max}}, t_p = 10\text{ ms}$	I_{TSM}	3300 A 2900 A
Grenzlastintegral	I²t-value	$t_{vj} = 25^{\circ}\text{C}, t_p = 10\text{ ms}$ $t_{vj} = t_{vj\text{ max}}, t_p = 10\text{ ms}$	I^2t	54500 A²s 42000 A²s
Kritische Stromsteilheit	critical rate of rise of on-state current	$V_D \leq 67\% V_{\text{DRM}}, f = 50\text{ Hz}$ $i_{\text{GM}} = 0,6\text{ A}, di_{\text{G}}/dt = 0,6\text{ A}/\mu\text{s}$	$(di/dt)_{\text{cr}}$	160 Alus 1) 2)
Kritische Spannungssteilheit	critical rate of rise of off-state voltage	$t_{vj} = t_{vj\text{ max}}, V_D = 67\% V_{\text{DRM}}$	$(dv/dt)_{\text{cr}}$	B: 50 50 V/μs c*: 500 500 V/μs L: 500 50 V/μs M*: 1000 500 V/μs

Charakteristische Werte	Characteristic values			
Durchlaßspannung	on-state voltage	$t_{vj} = t_{vj\text{ max}}, i_T = 500\text{ A}$	V_T	max. 2,2 v
Schleusenspannung	threshold voltage	$t_{vj} = t_{vj\text{ max}}$	$V_{T(\text{TO})}$	1,2 v
Ersatzwiderstand	slope resistance	$t_{vj} = t_{vj\text{ max}}$	r_T	1,6 mΩ
Zündstrom	gate trigger current	$t_{vj} = 25^{\circ}\text{C}, V_D = 12\text{ V}$	I_{GT}	max. 150 mA
Zündspannung	gate trigger voltage	$t_{vj} = 25^{\circ}\text{C}, V_D = 12\text{ V}$	V_{GT}	max. 2 v
Nicht zündender Steuerstrom	gate non-trigger current	$t_{vj} = t_{vj\text{ max}}, V_D = 12\text{ V}$	I_{GD}	max. 10 mA
Nicht zündende Steuerspannung	gate non-trigger voltage	$t_{vj} = t_{vj\text{ max}}, V_D = 0,5 V_{\text{DRM}}$	V_{GD}	max. 0,25 V
Haltestrom	holding current	$t_{vj} = 25^{\circ}\text{C}, V_D = 12\text{ V}, R_A = 10\text{ }\Omega$	I_H	max. 250 mA
Einraststrom	latching current	$t_{vj} = 25^{\circ}\text{C}, V_D = 12\text{ V}, R_{\text{GK}} \geq 10\text{ }\Omega$ $i_{\text{GM}} = 0,6\text{ A}, di_{\text{G}}/dt = 0,6\text{ A}/\mu\text{s}, t_g = 20\text{ }\mu\text{s}$	I_L	max. 1 A
Vorwärts- u. Rückwärts-Sperrstrom	forward off-state and reverse Currents	$t_{vj} = t_{vj\text{ max}}, V_D = V_{\text{DRM}}, V_R = V_{\text{RRM}}$	i_D, i_R	max. 30 mA
Zündverzug	gate controlled delay time	$t_{vj} = 25^{\circ}\text{C}, i_{\text{GM}} = 0,6\text{ A}, di_{\text{G}}/dt = 0,6\text{ A}/\mu\text{s}$	t_{gd}	max. 1,4 μs
Freiwerdezeit	circuit commutated turn-off time	siehe Techn. Erl./see Techn. Inf.	t_q	S: max. 18 μs E: max. 20 μs F: max. 25 μs

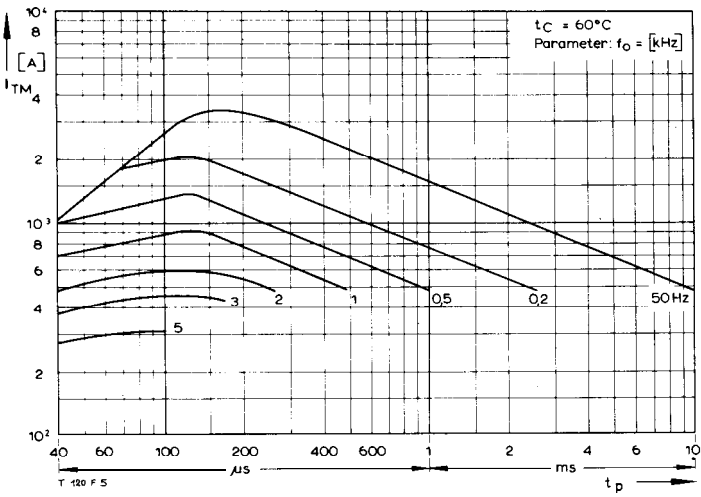
Thermische Eigenschaften	Thermal properties			
Innerer Wärmewiderstand	thermal resistance, junction to case	$\Theta = 180^{\circ}\text{ el, sin DC}$	R_{thJC}	max. 0,2 °C/W max. 0,186 °C/W
Höchstzul. Sperrschichttemperatur	max. junction temperature		$t_{vj\text{ max}}$	125°C
Betriebstemperatur	Operating temperature		$t_{\text{c op}}$	-40 ... + 125°C
Lagertemperatur	storage temperature		t_{stg}	-40 ... + 150°C

Mechanische Eigenschaften	Mechanical properties			
Si-Element mit Druckkontakt	Si-pellet with pressure contact		M	20 Nm
Anzugsdrehmoment	tightening torque		G	typ. 150 g
Gewicht	weight			8 mm
Kriechstrecke	Creepage distance			C
Feuchteklasse	humidity classification	DIN 40040		50 m/s²
Schwingfestigkeit	Vibration resistance	f = 50 Hz		
Maßbild B	outline B	DIN 41892-204B3		Seite/page 154

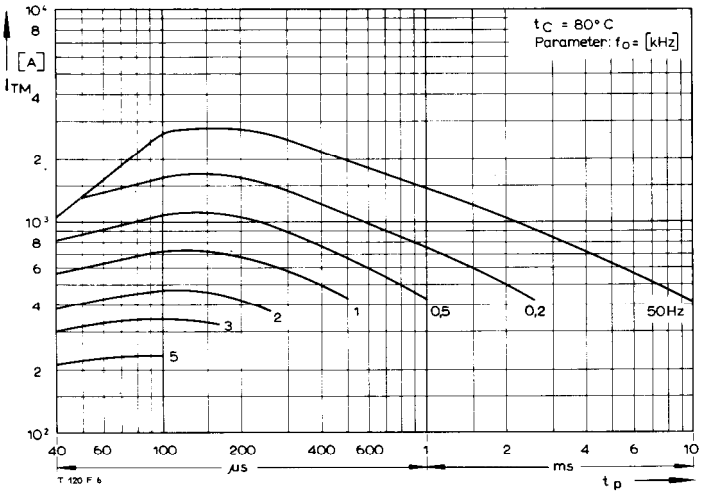
* Für größere Stückzahlen bitte Liefertermin erfragen/Delivery for larger quantities on request

1) Werte nach DIN IEC 747-6 (ohne vorausgehende Kommutierung)/Values to DIN IEC 747-6 (without prior commutation)

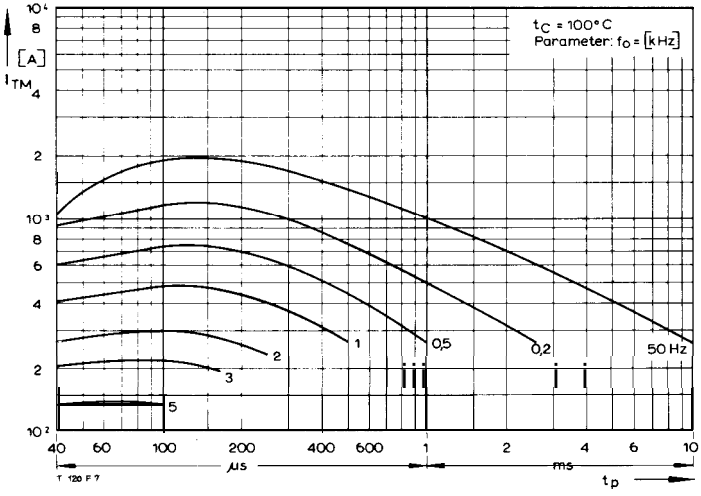
2) Unmittelbar nach der Freiwerdezeit, vgl. Meßbedingungen für t_q /Immediately after circuit commutated turn-off time, see Parameters t_q



BildFig. 1



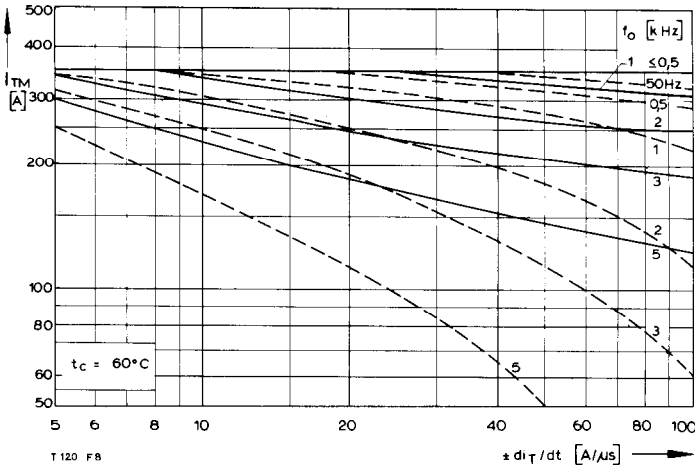
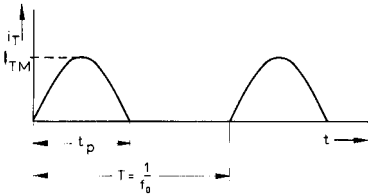
BildFig. 2



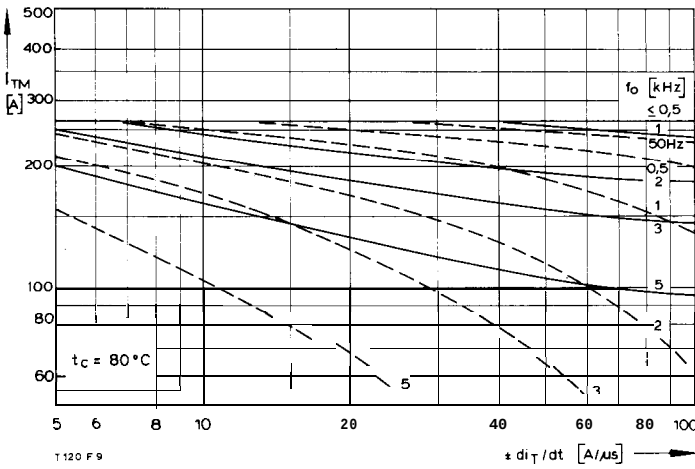
BildFig. 3

BildFig. 1, 2, 3
Steuer-generator/pulse generator:
 $I_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

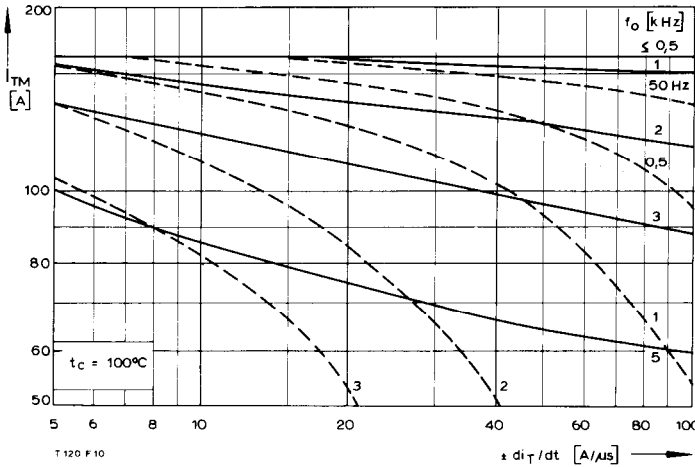
RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 V_{DM} [\text{V}]$
 $C \leq 0,15 \mu\text{F}$
 $V_{DM} \leq 0,67 V_{DRM}$



BildFig. 4



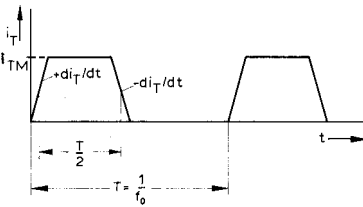
BildFig. 5

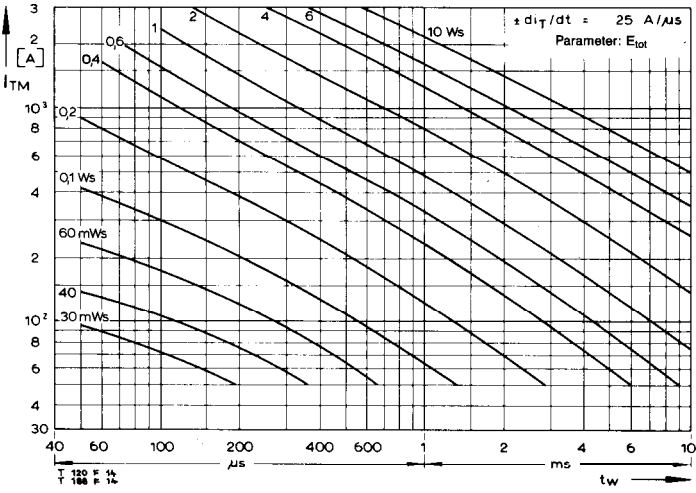


BildFig. 6

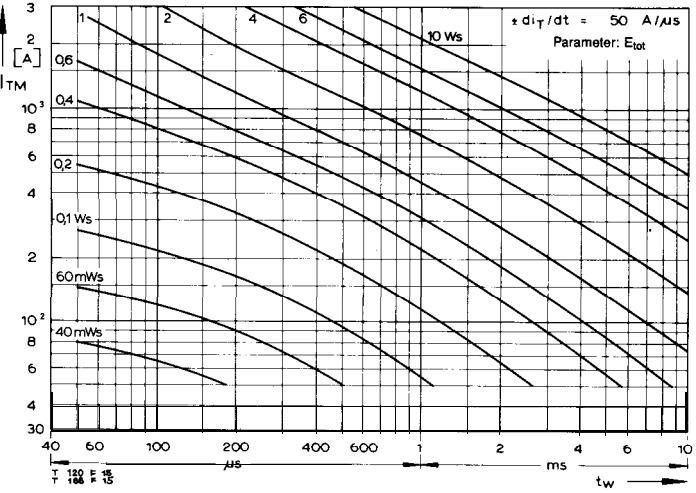
BildFig. 4, 5, 6
Steuer-generator/pulse generator:
 $I_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 V_{DM} [\text{V}]$
 $C \leq 0,22 \mu\text{F}$
 $V_{DM} \leq 0,67 V_{DRM}$
 $dv_R/dt \leq 600 \text{ V}/\mu\text{s}$
 $V_{RM} \leq 0,67 V_{RRM}$

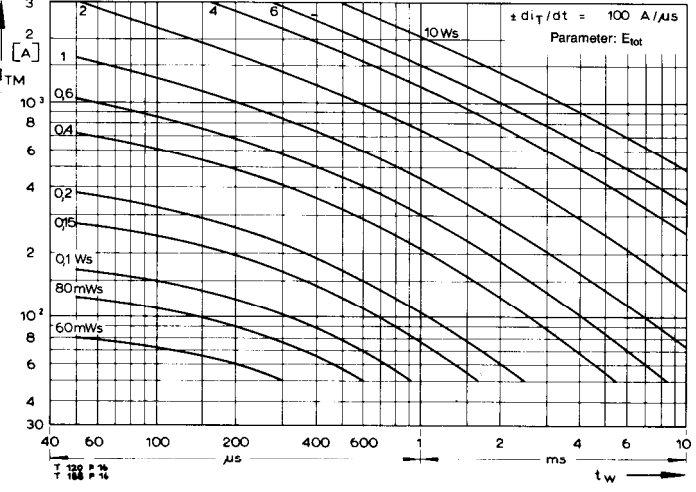




BildFig. 10



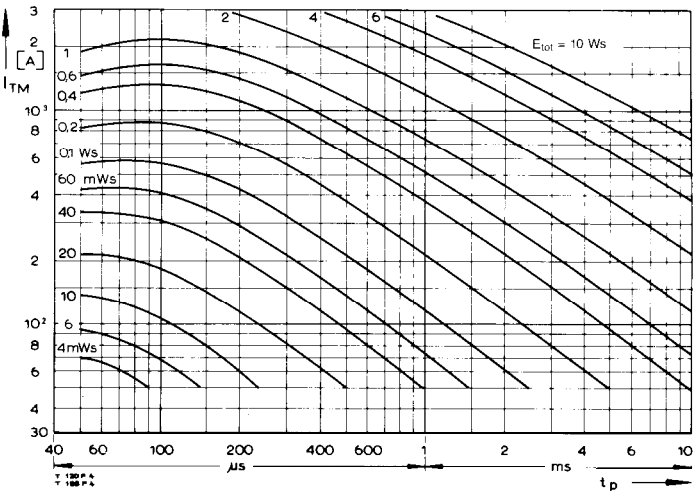
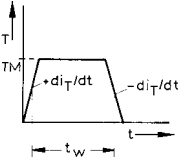
BildFig. 11



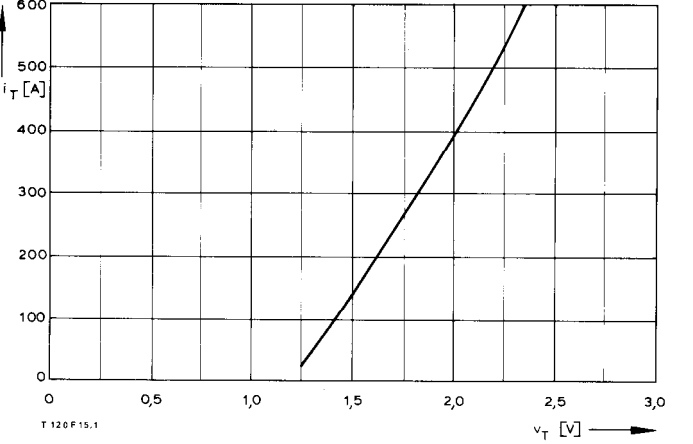
BildFig. 12

BildFig. 10, 11, 12
Steuer-generator/pulse generator:
 $i_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

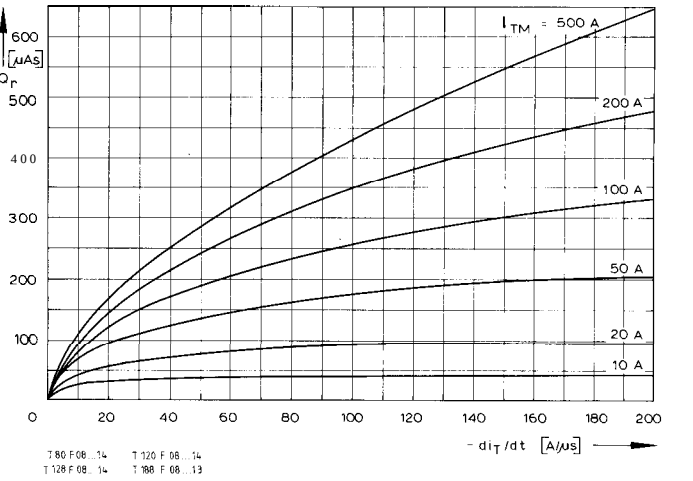
RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 \text{ } v_{DM} [\text{V}]$
 $C \leq 0,22 \mu\text{F}$
 $v_{DM} \leq 0,67 \text{ } v_{D.}$
 $dv_T/dt \leq 600 \text{ V}/\mu\text{s}$
 $v_{RM} \leq 0,67 \text{ } v_{RRM}$



BildFig. 13



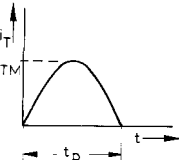
BildFig. 14

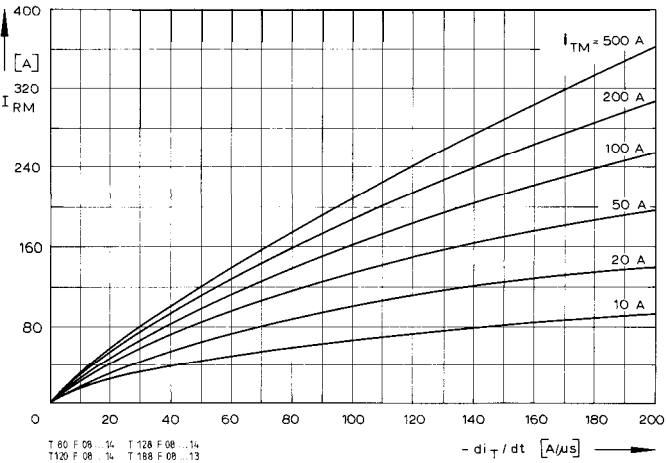


BildFig. 15

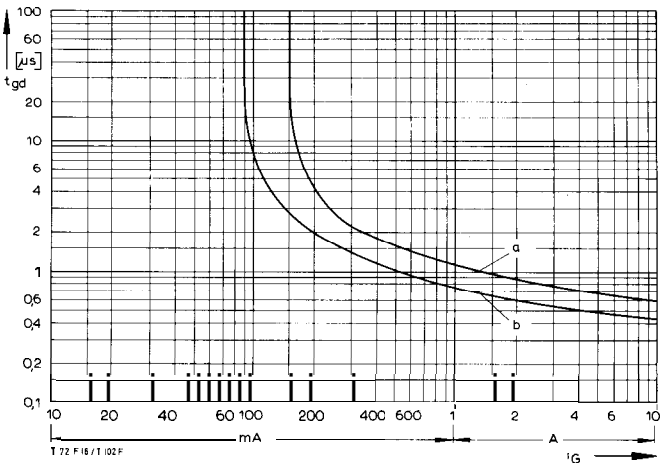
(zu Bild/to Fig. 13)
Steuer-generator/pulse generator:
 $i_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 \text{ } v_{DM} [\text{V}]$
 $C \leq 0,15 \mu\text{F}$

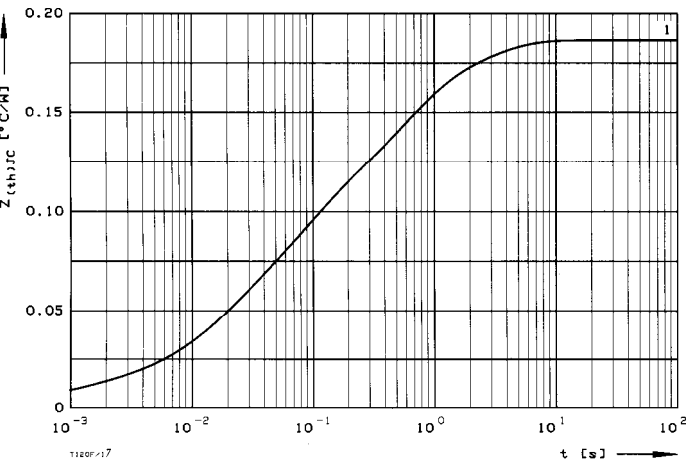




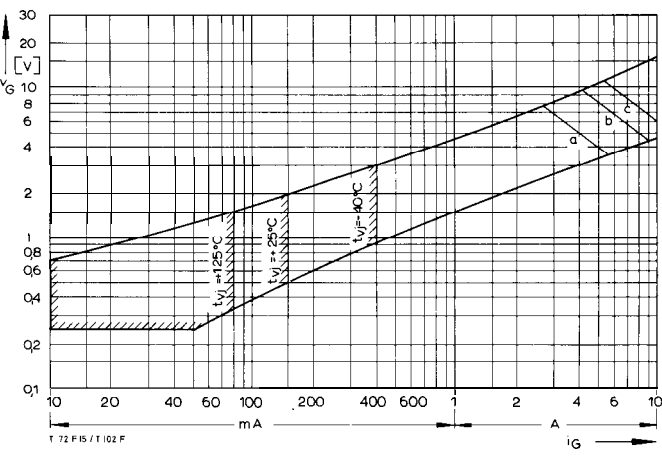
Bild/ Fig. 16
Rückstromspitze $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $V_R = 0,5 V_{RRM}$, $V_{RM} = 0,8 V_{RRM}$
Peak reverse recovery current $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $V_R = 0,5 V_{RRM}$, $V_{RM} = 0,8 V_{RRM}$
Parameter: Durchlaßstrom/On-state current I_{TM}



Bild/ Fig. 18
Zündverzugs/ Gate controlled delay time $t_{gd} = f(I_{GM})$, $t_{vj} = 25^\circ\text{C}$, $di_G/dt = i_{GM}/1 \mu\text{s}$
a – Maximaler Verlauf/Limiting characteristic
b – Typischer Verlauf/Typical characteristic



Bild/ Fig. 17
Transienter Innerer Wärmewiderstand $Z_{thJC} = f(t)$, DC
Transient thermal impedance $Z_{thJC} = f(t)$, DC



Bild/ Fig. 19
Steuercharakteristik mit Zündbereichen/ Gate Characteristic with triggering areas
 $V_G = f(I_G)$, $V_o = 12$ V

Parameter:	a	b	c
Steuerimpulsdauer/Trigger pulse duration t_g [ms]	10	1	0,5
Höchstzulässige Spitzensteuerverlustleistung/ Max. rated peak gate power dissipation P_{GM} [W]	20	40	60

Analytische Elemente des transienten Wärmewiderstandes Z_{thJC} für DC Analytical elements of transient thermal impedance Z_{thJC} for DC							
Pos. n	1	2	3	4	5	6	7
R_{thn} [$^\circ\text{C}/\text{W}$]	0,008134	0,032536	0,054253	0,061911	0,029501		
τ_n [s]	0,000814	0,013651	0,066196	0,496428	2,293634		

Analytische Funktion/analytical function:

$$Z_{thJC} = \sum_{n=1}^{n_{max}} R_{thn} (1 - \text{EXP} (-t/\tau_n))$$